		[redacted]		

[redacted]

	℃					
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					

25℃ unless otherwise spe

FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

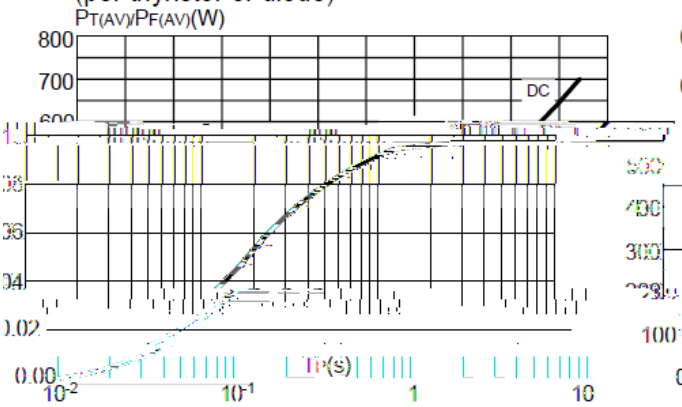


FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)

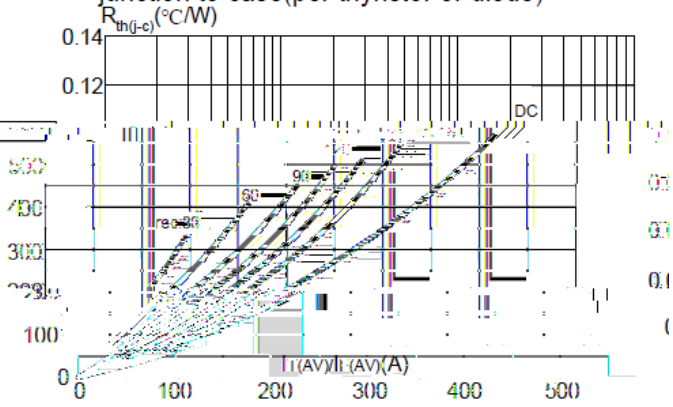


FIG.3: Forward characteristics (per thyristor or diode)

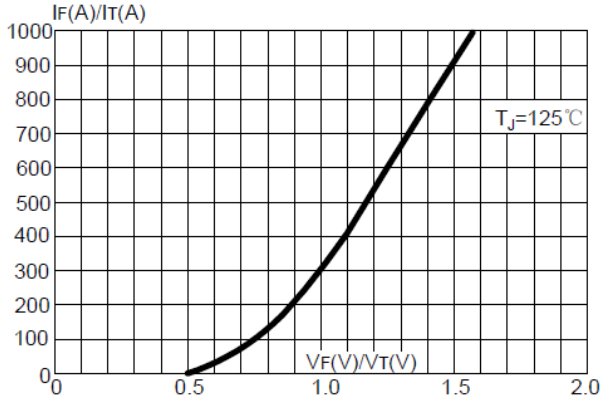


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

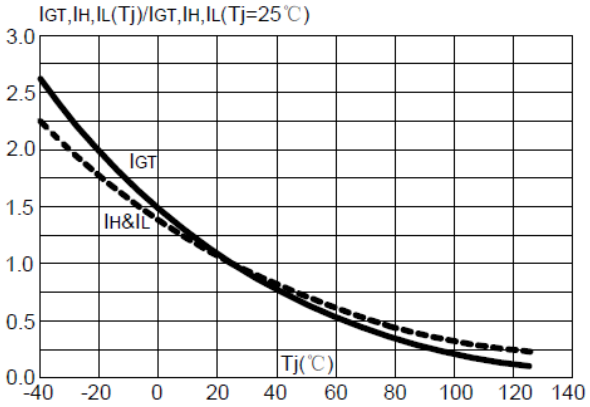
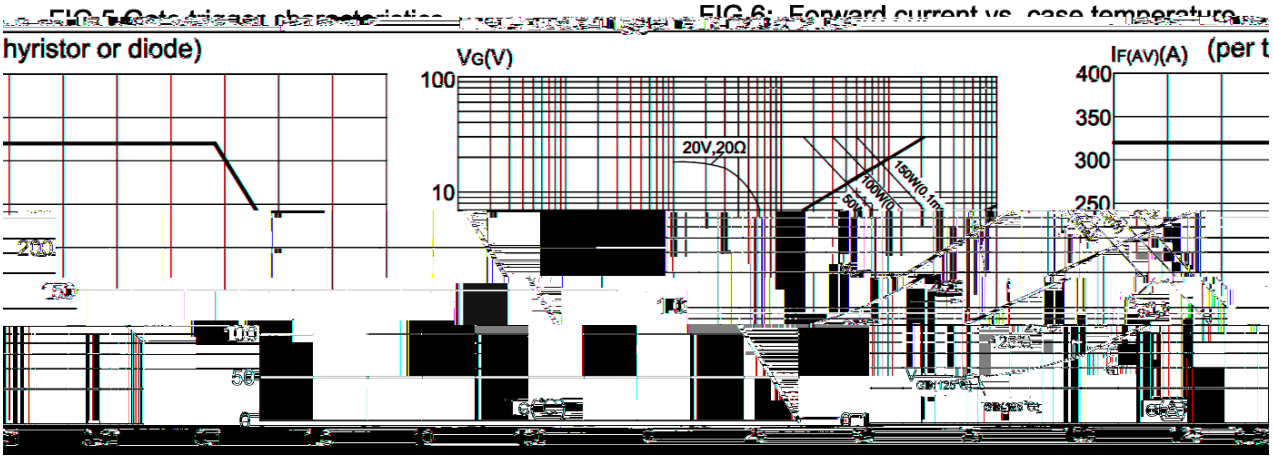
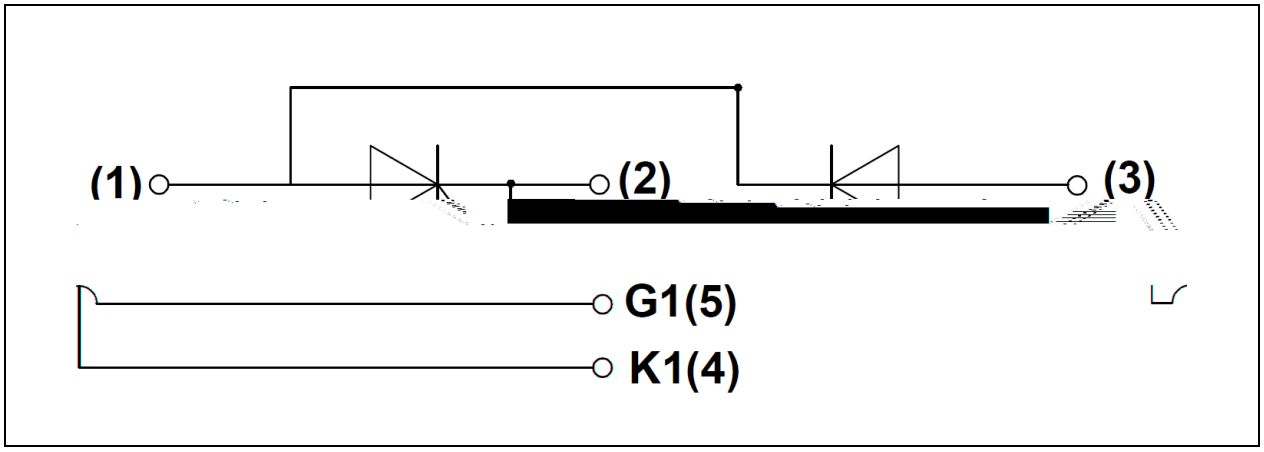
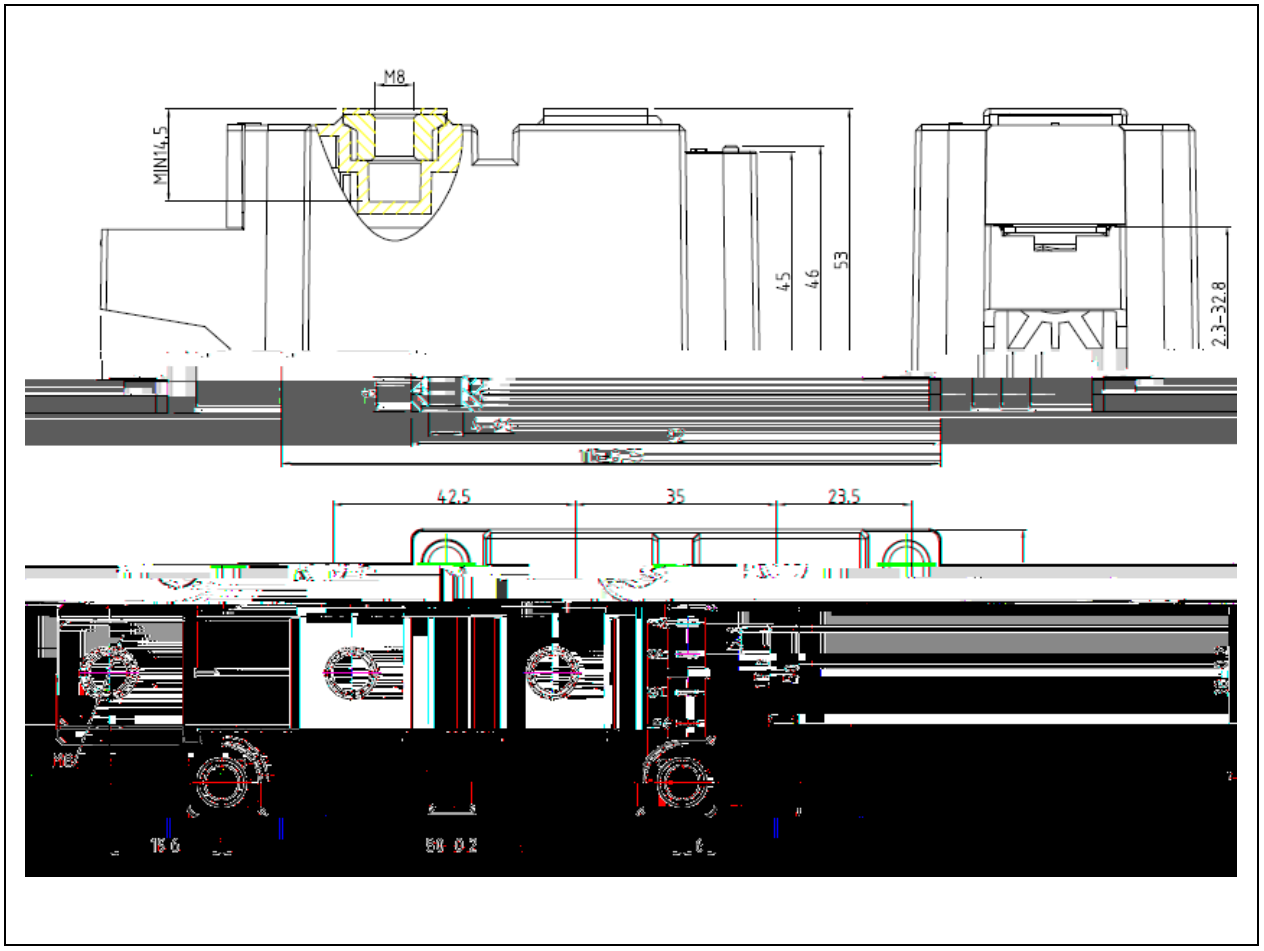


FIG.5 Gate trigger characteristics (per thyristor or diode)

FIG.6: Forward current vs. case temperature (per t




(1)
(2)
(3)
G1(5)
K1(4)


M8
MIN14.5
45
46
53
2.3-32.8
42.5
35
23.5